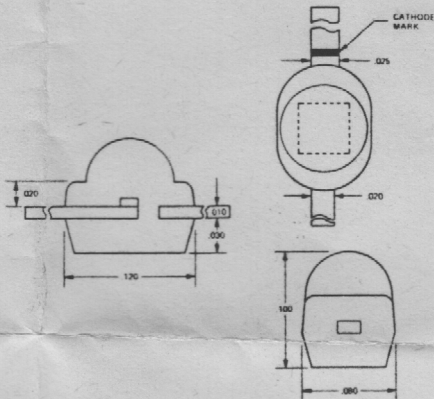
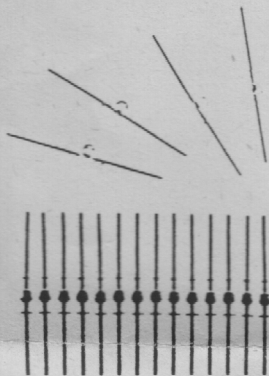


DIMENSIONS (in inches, Nominal)



IR-Lit 60

INFRARED EMITTER

- Spectrally matched to Silicon Sensors
- Maximum package strength consistent with mounting on .087" centers
- Optical Encoding source
- Positioning and counting source
- Solid State reliability

The IR-Lit 60 is a gallium arsenide infrared emitting diode. On forward bias, it emits a spectrally narrow intense band of radiation peaking at 900 nm (the peak sensitivity point of silicon detectors). The packaging of this unit permits close-spacing in linear arrays. Its low cost and volume producibility opens new areas of use anywhere an infrared source is desirable.

Maximum Ratings

Power Dissipation, 25°C	75 mW
Derate Linearly from 25°C	1.0 mW/°C
Storage and Operating Temperature	-55° to +100°C
Reverse Voltage	3.0 V
DC forward current	50 mA
Lead solder time @ 260°C (Note 1)	10 sec

Opto-Electronic Characteristics

Parameter	Min	Typ	Max	Units	Test Conditions
Total External Radiated Power	400	550		μW	I _F = 50 mA
Forward Voltage	1.3	1.5		V	I _F = 50 mA
Reverse Current	.15	10		μA	V _R = 3.0 V
Radiation Rise and Fall		1.0		n sec	
Capacitance		80		pF	V=0
Peak Emission Wave Length		900		nm	
Spectral Line Half-Width		40		nm	

NOTE:

- 1) The leads were immersed in 260° molten solder to a distance 1/16" from the body of the device per MIL-S-750.